

AFGH4L40T120RWD

AFGH4L40T120RWD

ELECTRICAL CHARACTERISTICS ($T_J = 25$ C unless otherwise specified) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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AFGH4L40T120RWD

TYPICAL CHARACTERISTICS

AFGH4L40T120RWD

TYPICAL CHARACTERISTICS

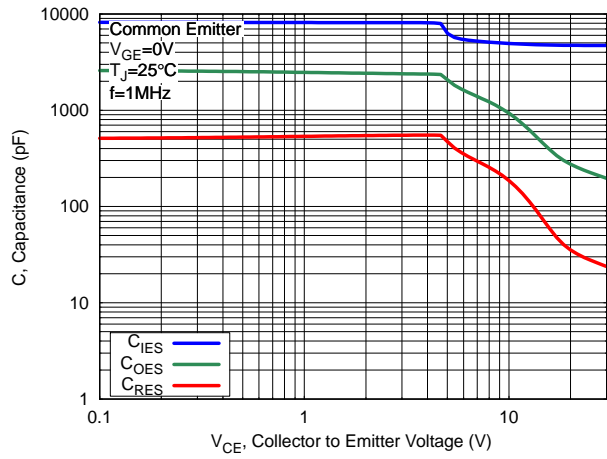


Figure 7. Capacitance Characteristics

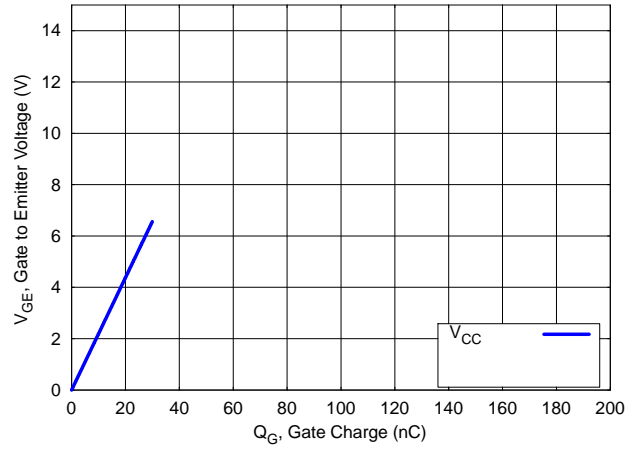


Figure 8. Gate Charge Characteristics

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TYPICAL CHARACTERISTICS

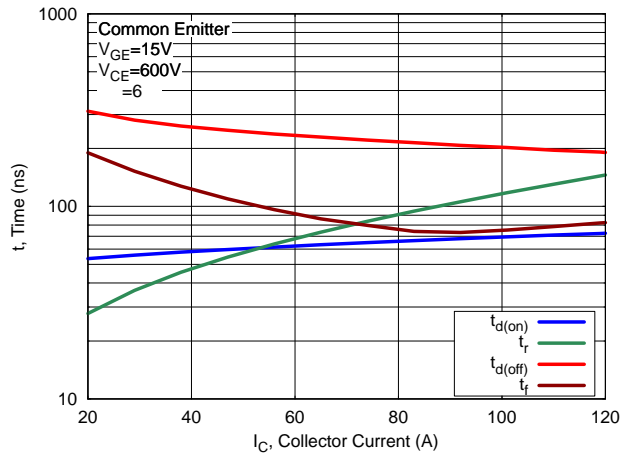


Figure 13. Switching Time vs Collector Current

Figure 14. Switching Time vs Collector Current

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